

CentralTM Semiconductor Corp.

145 Adams Avenue, Hauppauge, NY 11788 USA
Tel: (631) 435-1110 • Fax: (631) 435-1824

Manufacturers of World Class Discrete Semiconductors

CQ220-8B
CQ220-8D
CQ220-8M
CQ220-8N

8.0 AMP TRIAC
200 THRU 800 VOLTS

JEDEC TO-220AB CASE

DESCRIPTION

The CENTRAL SEMICONDUCTOR CQ220-8B series type is an Epoxy Molded Silicon Triac designed for full wave AC control applications featuring gate triggering in all four (4) quadrants.

MAXIMUM RATINGS (T_C = 25°C unless otherwise noted)

	SYMBOL	CQ220 -8B	CQ220 -8D	CQ220 -8M	CQ220 -8N	UNITS
Peak Repetitive Off-State Voltage	V _{DRM}	200	400	600	800	V
RMS On-State Current (T _C = 90°C)	I _{T(RMS)}		8.0			A
Peak One Cycle Surge (t = 10ms)	I _{TSM}		80			A
I ² t Value for Fusing (t = 10ms)	I ² t		32			A ² s
Peak Gate Power (tp = 10μs)	P _{GM}		40			W
Average Gate Power Dissipation	P _{G(AV)}		1.0			W
Peak Gate Current (tp = 10μs)	I _{GM}		4.0			A
Peak Gate Voltage (tp = 10μs)	V _{GM}		16			V
Critical Rate of Rise of On-State Current Repetitive (F = 50Hz)	di/dt		10			A/μs
Storage Temperature	T _{stg}		-40 to +150			°C
Junction Temperature	T _J		-40 to +110			°C
Thermal Resistance	θ _{J-A}		60			°C/W
Thermal Resistance	θ _{J-C}		3.2			°C/W

ELECTRICAL CHARACTERISTICS (T_C = 25°C unless otherwise noted)

SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNITS
I _{DRM}	Rated V _{DRM}			0.01	mA
I _{DRM}	Rated V _{DRM} , T _C = 110°C			0.50	mA
I _{GT}	V _D = 12V, R _L = 33Ω, QUAD I,II,III			25	mA
I _{GT}	V _D = 12V, R _L = 33Ω, QUAD IV			50	mA
I _H	I _T = 100mA			25	mA
V _{GT}	V _D = 12V, R _L = 33Ω, QUAD I,II,III,IV			1.50	V
V _{TM}	I _{TM} = 11A, tp = 10ms			1.75	V
dv/dt	V _D = 2/3 V _{DRM} , R _{GK} = ∞, T _C = 110°C	100			V/μs